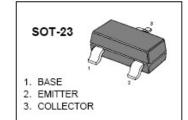


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TRANSISTOR (NPN)



MAXIMUM RATINGS (T_A=25°C unless otherwise noted)

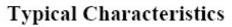
Symbol	Parameter	Value	Units V	
V _{CBO}	Collector-Base Voltage	40		
Vceo	Collector-Emitter Voltage	25	v	
VEBO	Emitter-Base Voltage	5	v	
Ic	Collector Current -Continuous	0.5	А	
Pc	Collector Dissipation	0.3	W	
Tj	Junction Temperature	150	°C	
T _{stg}	Storage Temperature	-55-150	°C	

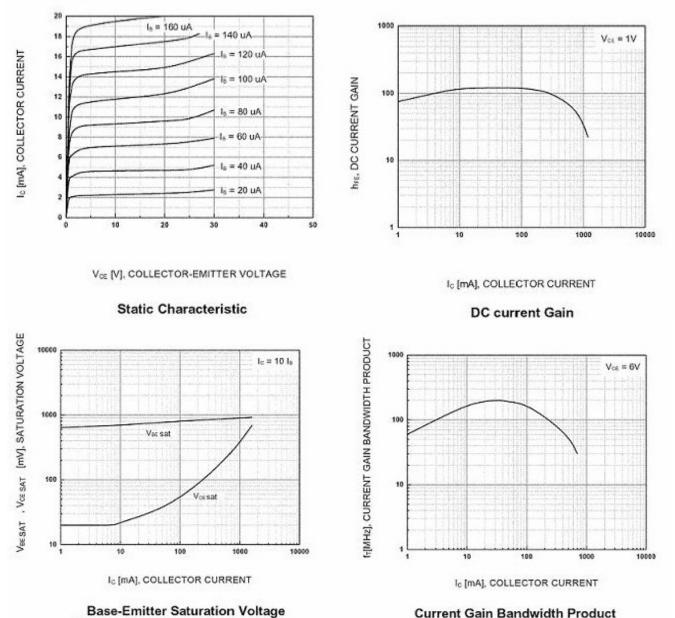
ELECTRICAL CHARACTERISTICS (Tamb=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	ТҮР	MAX	UNIT
Collector-base breakdown voltage	V _{(BR)CBO}	Ic= 100µA, IE=0	40			v
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C =1mA, I _B =0	25			v
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =100μΑ, I _C =0	5			v
Collector cut-off current	Ісво	V _{CB} =40 V, I _E =0			0.1	μA
Collector cut-off current	I _{CEO}	V _{CB} =20V, I _E =0			0.1	μA
Emitter cut-off current	I _{EBO}	V _{EB} = 5V, I _C =0			0.1	μA
	HFE(1)	V _{CE} =1V, I _C = 50mA	100		600	
DC current gain	H _{FE(2)}	V _{CE} =1V, I _C = 500mA	50			
Collector-emitter saturation voltage	V _{CE} (sat)	I _C =500 mA, I _B = 50mA			0.6	v
Base-emitter saturation voltage	V _{BE} (sat)	Ic=500 mA, IB= 50mA			1.2	v
Transition frequency	f⊤	V _{CE} =6V, I _C = 20mA f=30MHz	150			MHz



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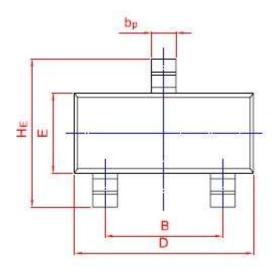


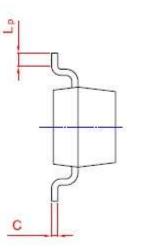
Collector-Emitter Saturation Voltage

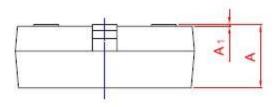


PACKAGE OUTLINE

Plastic surface mounted package; 3 leads







UNIT	A	в	bp	С	D	Е	HE	A1	Lp
mm	1.40	2.04	0.50	0.19	3.10	1.65	3.00	0.100	0.50
	0.95	1.78	0.35	0.08	2.70	1.20	2.20	0.013	0.20

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